



**AZ Electronic Materials**

# **AZ 193nm/248nm Top Anti-Reflective Coating**

General Products Update  
January 2005

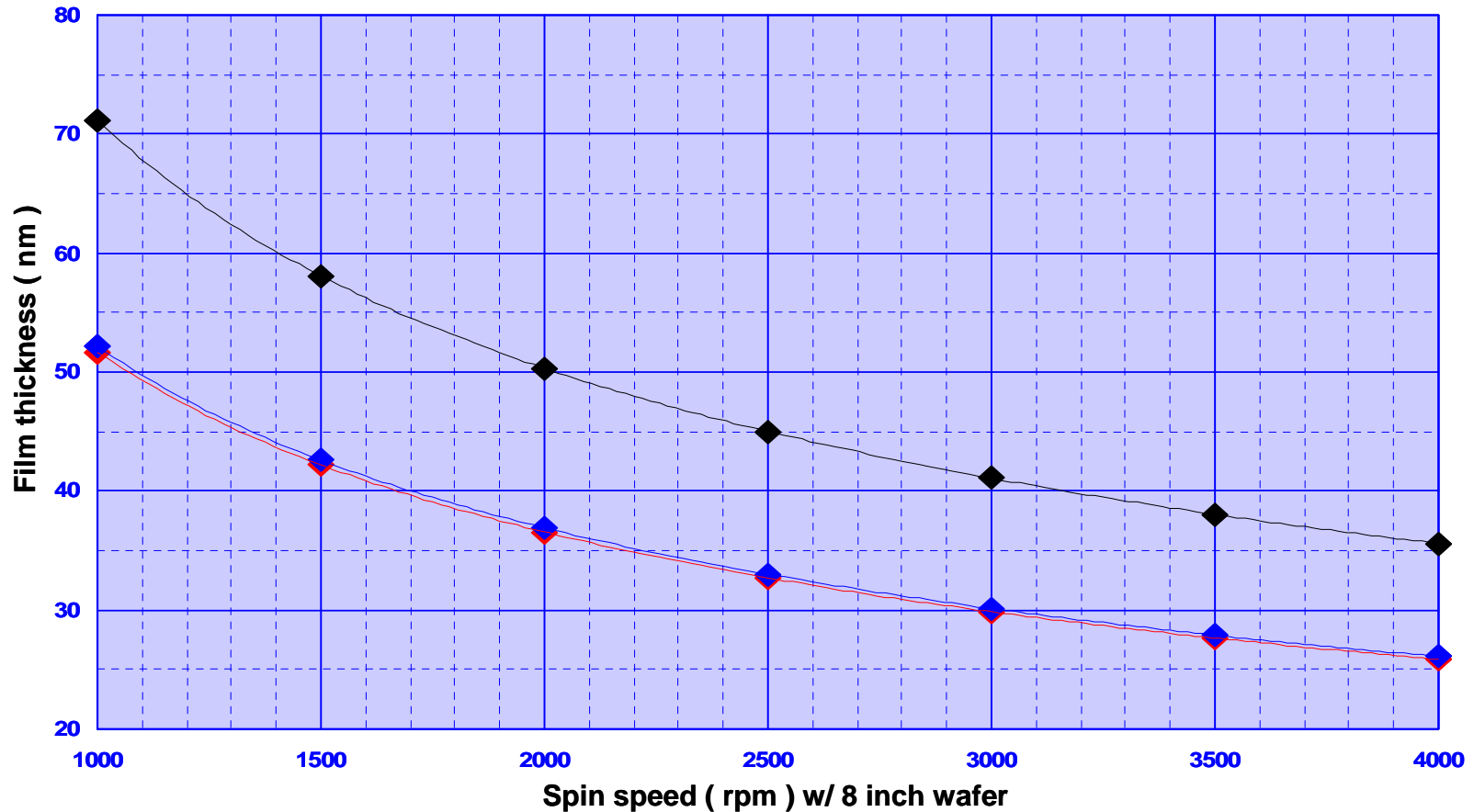
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# AZ 193nm/248nm T.A.R.C. Series

## Category and Capability

	AZ AQUATAR-III Coating	EXP AQUATAR-VIII-A Coating	AZ AQUATAR-VI Coating	Experimental Material (TBD)
Application	248nm Process	248nm Process Applicable for 193nm Process	193nm Process	193nm Process
Features	Existing Standard Material for 248nm Process (POFS contained)	Newly Developed PFOS/A Free Material	Existing Standard Material for 193nm Process (PFOS contained)	Newly Developed PFOS/A Free Material
Refractive Index	n@248nm : 1.43 k@248nm : 0.00	n@248nm : 1.44 ( n@193nm : 1.51 ) k@248nm : 0.00 ( k@193nm : 0.0043 )	n@193nm : 1.45 k@193nm : 0.084 ( n@248nm : 1.44 )	n@193nm : 1.4x (TBD) k@193nm : 0.0x (TBD)
Cauchy Coefficients	A = 1.381 B = 0.00647 $\mu\text{m}^2$ C = 0.00 $\mu\text{m}^4$	A = 1.3839 B = 0.0050346 $\mu\text{m}^2$ C = 0.00 $\mu\text{m}^4$	A = 1.379 B = 0.00262 $\mu\text{m}^2$ C = 0.00 $\mu\text{m}^4$	A = (TBD) B = (TBD) C = (TBD)

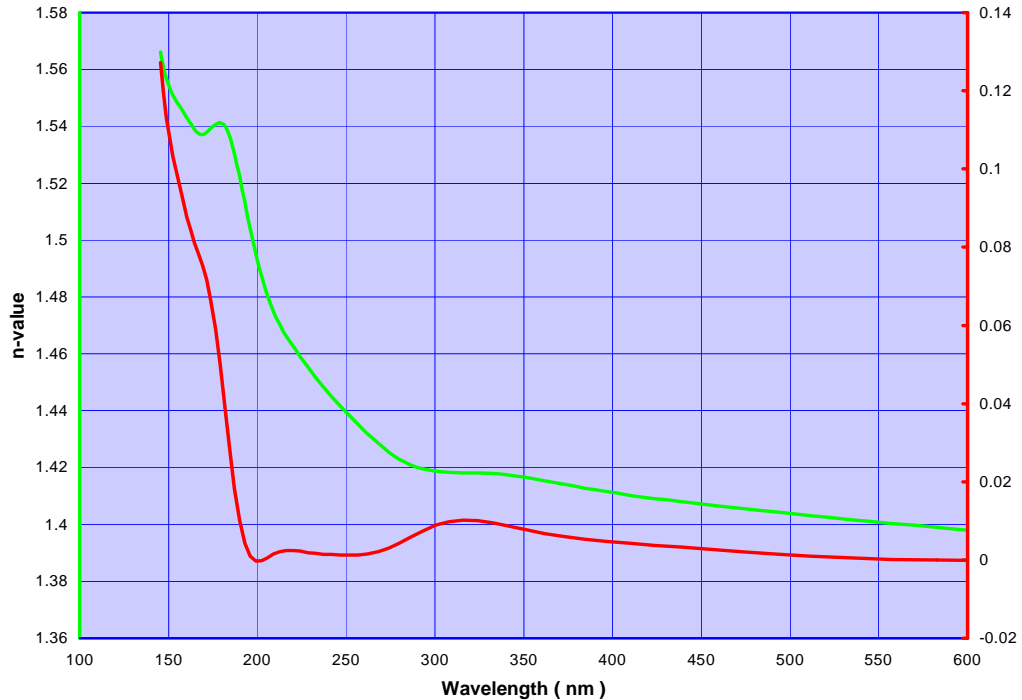
# AQUATAR-III & EXP AQUATAR-VIII-A Series Spin Curve



◆ EXP AQUATAR-VIII-A Coating 30    ◆ AQUATAR-III Coating 33    ◆ AQUATAR-III Coating 45

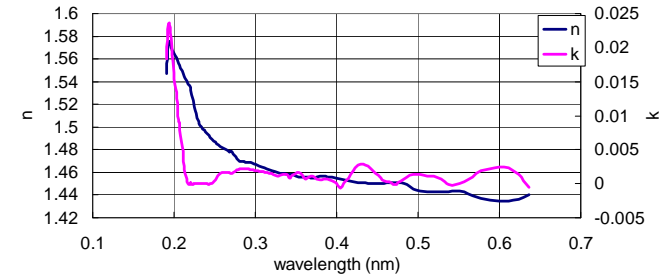
# Comparison of n/k value EXP AQUATAR-VIII-A vs. Competitive TARC

**EXP AQUATAR-VIII-A**



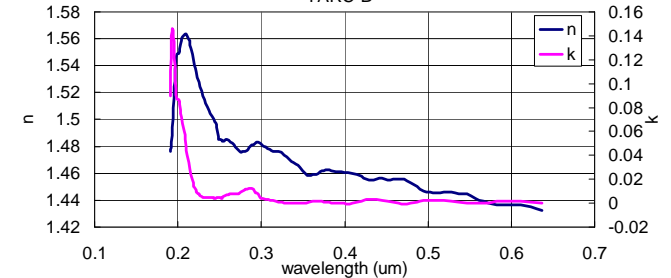
Ellipsometer : J. A. Woollam VUV-VASE  
 Film thickness: 45nm  
 n@248nm : 1.440  
 k@248nm : 0  
 Cauchy parameters(0.5um-0.65um):  
 A=1.3839, B=0.0050346, C=0

**TARC-A**



**TARC-A**  
 n@248nm : 1.48  
 k@248nm : 0.00

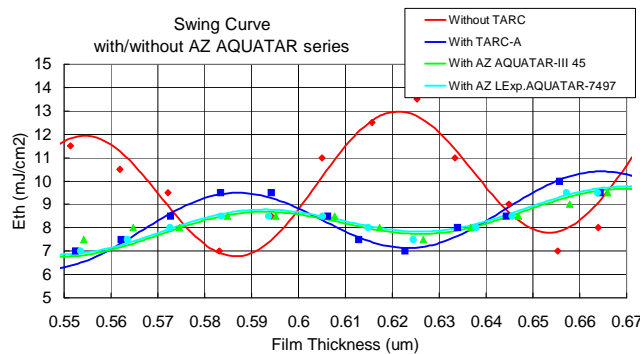
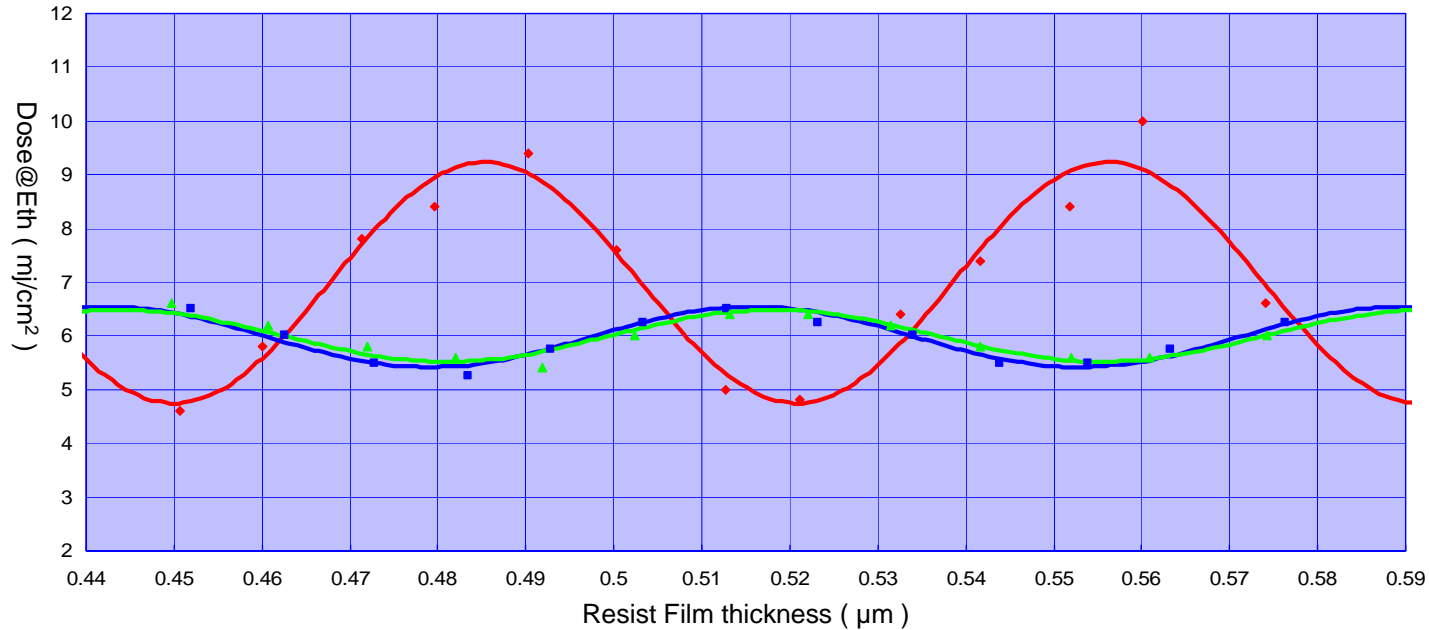
**TARC-B**



**TARC-B**  
 n@248nm : 1.48  
 k@248nm : 0.0049

# Swing Suppression Effect

## EXP AQUATAR-VIII-A vs. AZ AQUATAR-III



### Swing Suppression

**EXP AQUATAR-VIII-A : 86.5%**

**AZ AQUATAR-III : 86.5%**

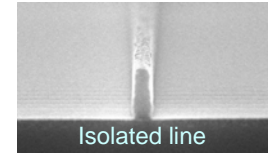
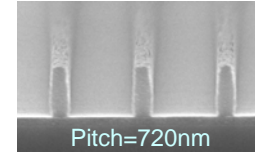
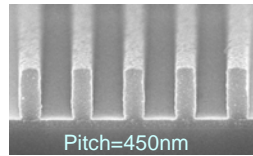
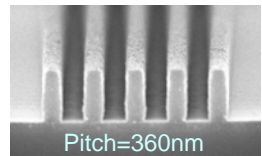
**TARC-A : 65.0%**

# EXP AQUATAR-VIII-A

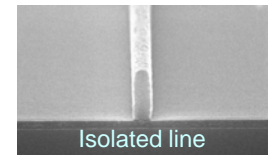
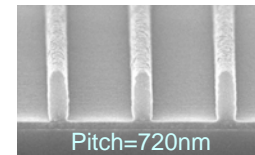
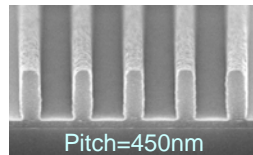
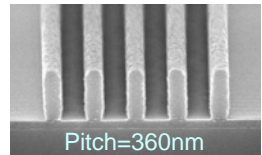
## Resist Compatibility – Acetal Type

### Line & Space Patterns : CD=180nm

w/o TARC



with  
AQUATAR-VIII-A

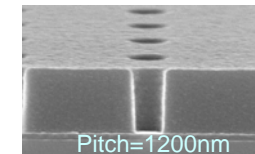
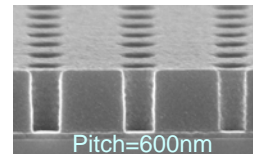
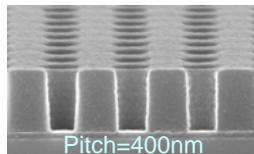


### **Process Conditions**

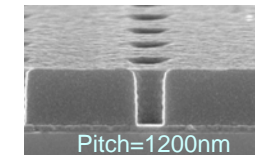
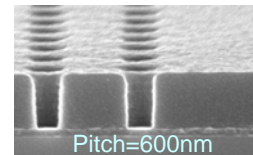
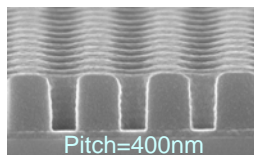
Film thickness : 45nm (TARC), 510nm (PR), 80nm (BARC)  
 SB : 90°C/60sec. (TARC), 90°C/90sec. (PR), 180°C/60sec. (BARC), PEB : 110°C/60sec  
 Exposure : 0.63NA/0.65sigma, Mask : Binary, Development : 2.38%TMAH 60sec.

### Contact Patterns : CD=200nm

w/o TARC



with  
AQUATAR-VIII-A



### **Process Conditions**

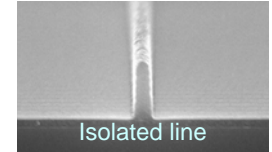
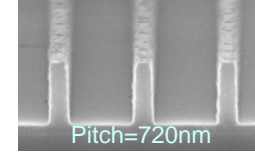
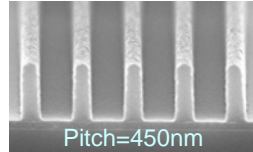
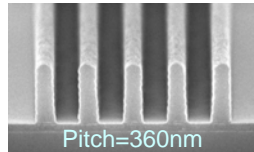
Film thickness : 45nm (TARC), 585nm (PR), 80nm (BARC)  
 SB : 90°C/60sec. (TARC), 90°C/60sec. (PR), 180°C/60sec. (BARC), PEB : 120°C/60sec  
 Exposure : 0.63NA/ 1/2annular, Mask : HT-PSM, Development : 2.38%TMAH 60sec.

# EXP AQUATAR-VIII-A

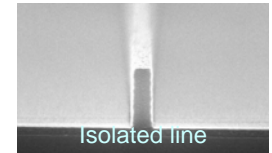
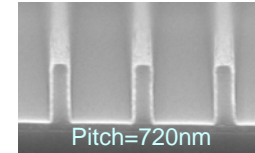
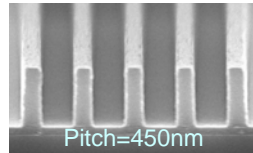
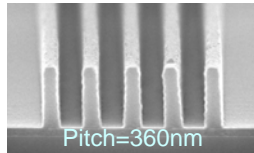
## Resist Compatibility – ESCAP Type

### Line & Space Patterns : CD=180nm

w/o TARC



with  
AQUATAR-VIII-A

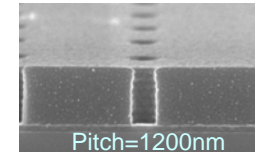
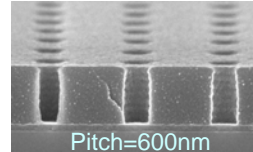
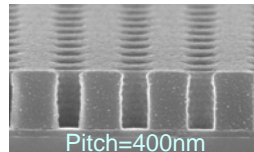


### **Process Conditions**

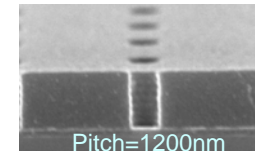
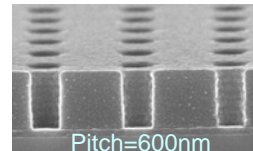
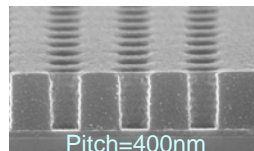
Film thickness : 45nm (TARC), 540nm (PR), 80nm (BARC)  
 SB : 90°C/60sec. (TARC), 130°C/60sec. (PR), 180°C/60sec. (BARC), PEB : 110°C/60sec  
 Exposure : 0.63NA/0.65sigma, Mask : Binary, Development : 2.38%TMAH 60sec.

### Contact Patterns : CD=200nm

w/o TARC



with  
AQUATAR-VIII-A



### **Process Conditions**

Film thickness : 45nm (TARC), 522nm (PR), 80nm (BARC)  
 SB : 90°C/60sec. (TARC), 120°C/90sec. (PR), 180°C/60sec. (BARC), PEB : 130°C/60sec  
 Exposure : 0.63NA/ 1/2annular, Mask : HT-PSM, Development : 2.38%TMAH 60sec.

# AZ AQUATAR-III Coating CD Uniformity Improvement Effect

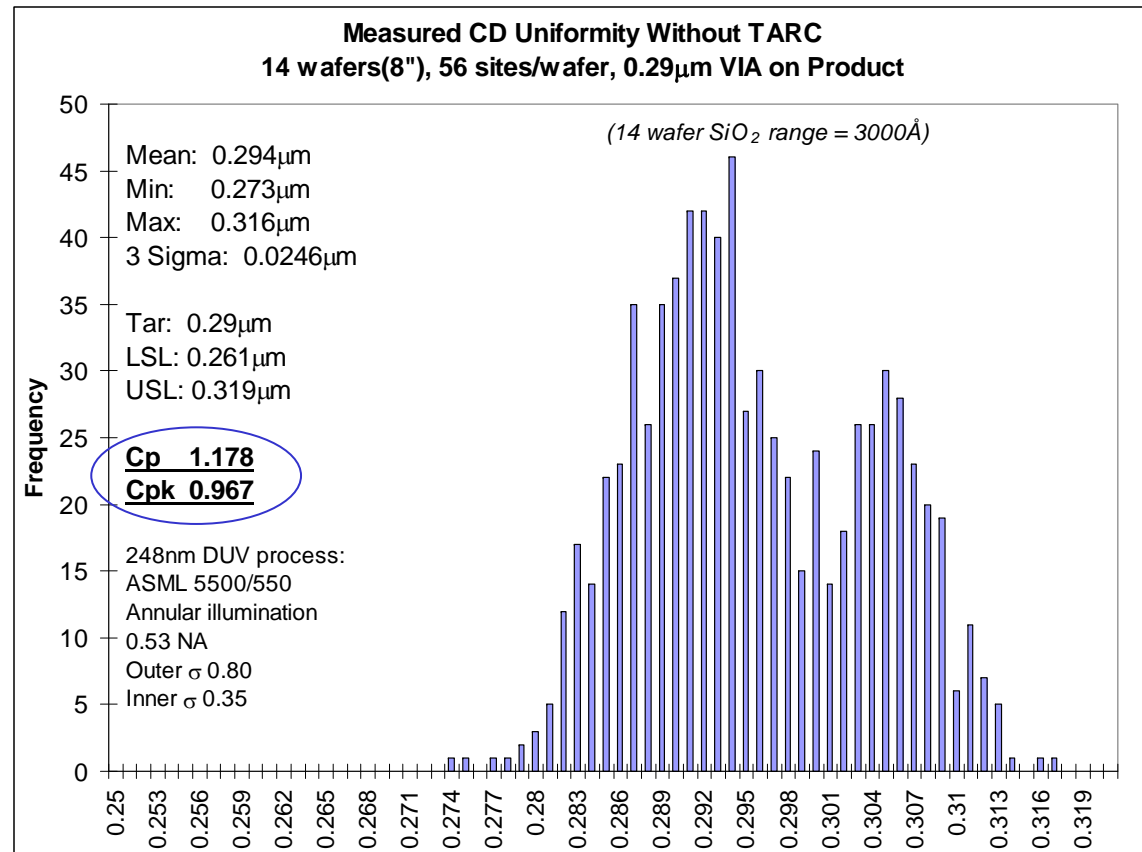
## without AZ AQUATAR-III

### Process Conditions:

14 wafers with  
topography

Oxide thickness  
increment of  $\sim 250\text{\AA}$   
per wafer for  $3000\text{\AA}$   
range across all 14  
wafers (worst CMP  
lot to lot process  
variation prediction)

DUV resist process  
without TARC.





# AZ AQUATAR-III Coating CD Uniformity Improvement Effect

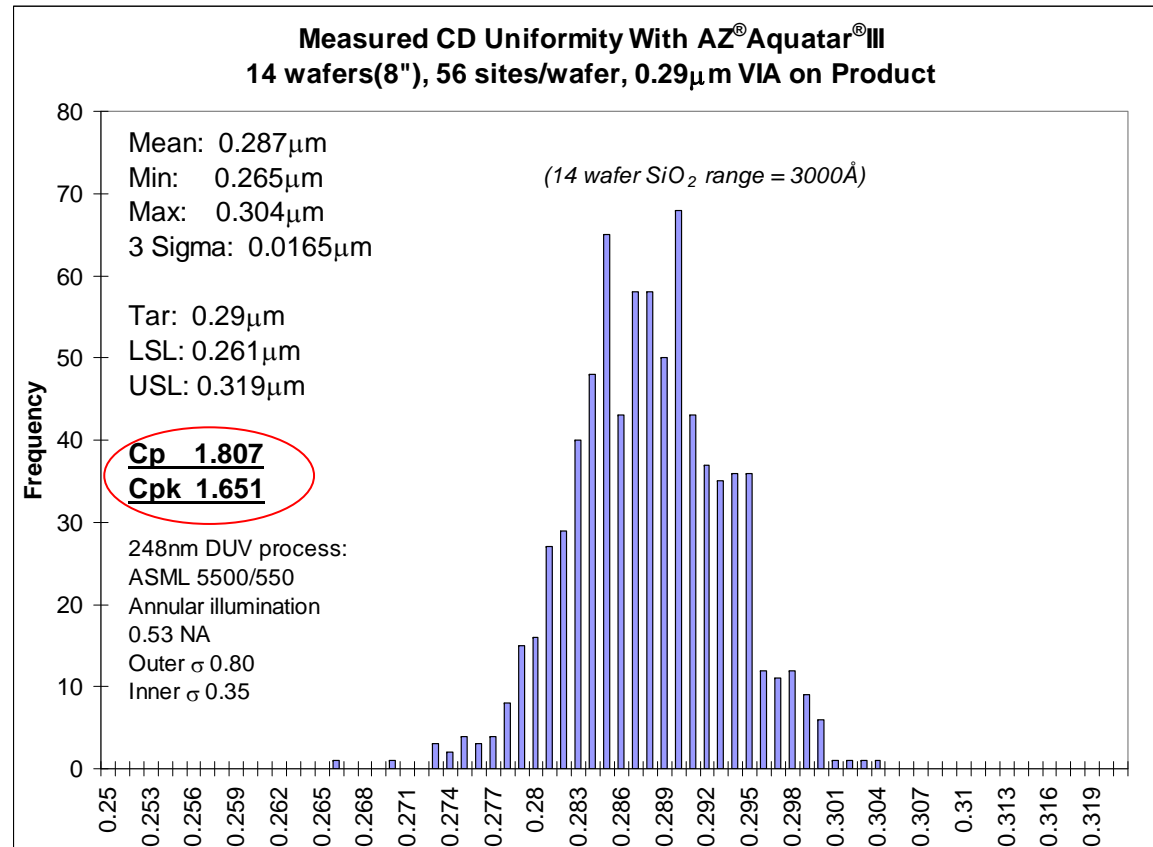
## without AZ AQUATAR-III

### Process Conditions:

14 wafers with  
topography

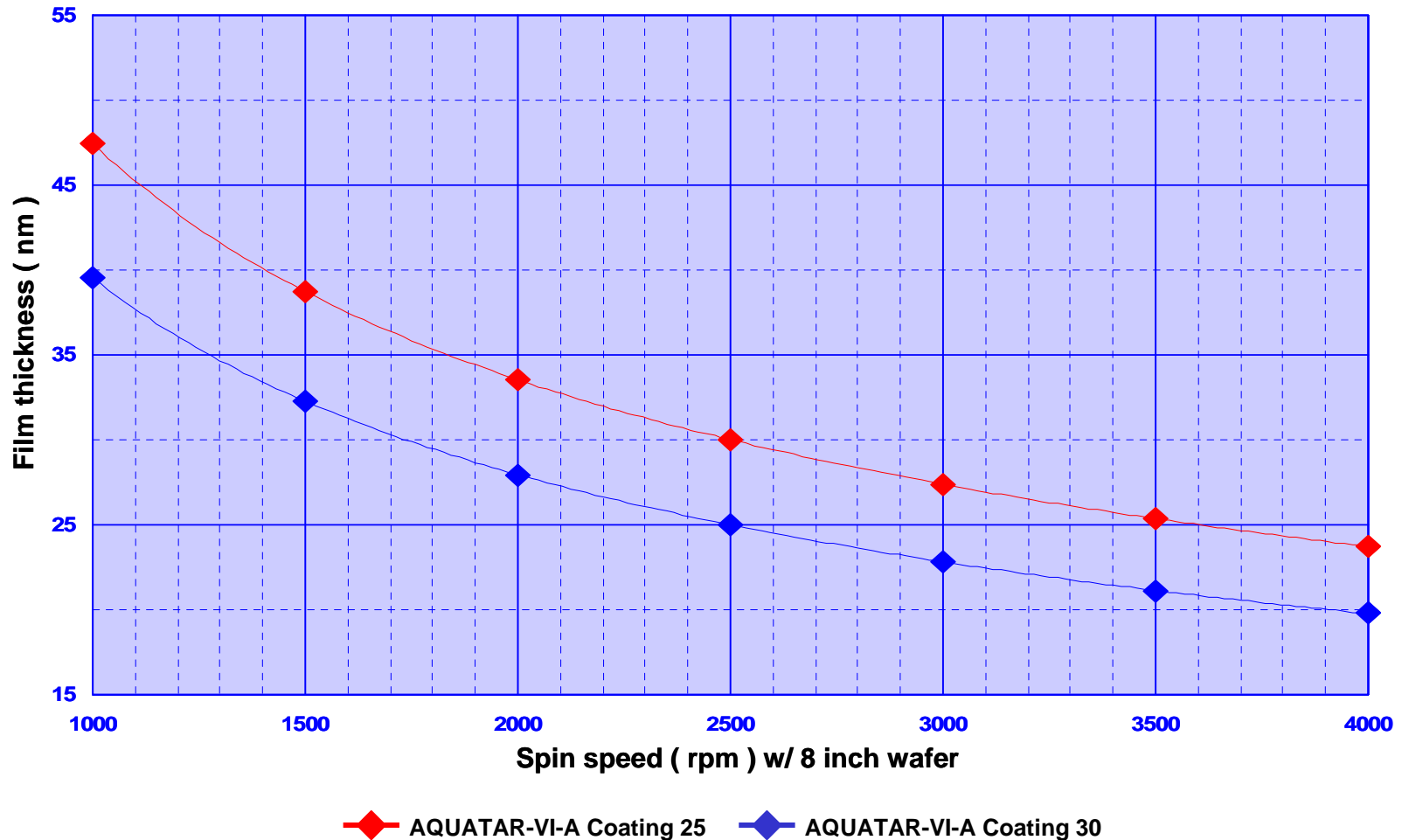
Oxide thickness  
increment of  $\sim 250\text{\AA}$   
per wafer for  $3000\text{\AA}$   
range across all 14  
wafers (worst CMP  
lot to lot process  
variation prediction)

DUV resist process  
with AZ AQUATAR-III



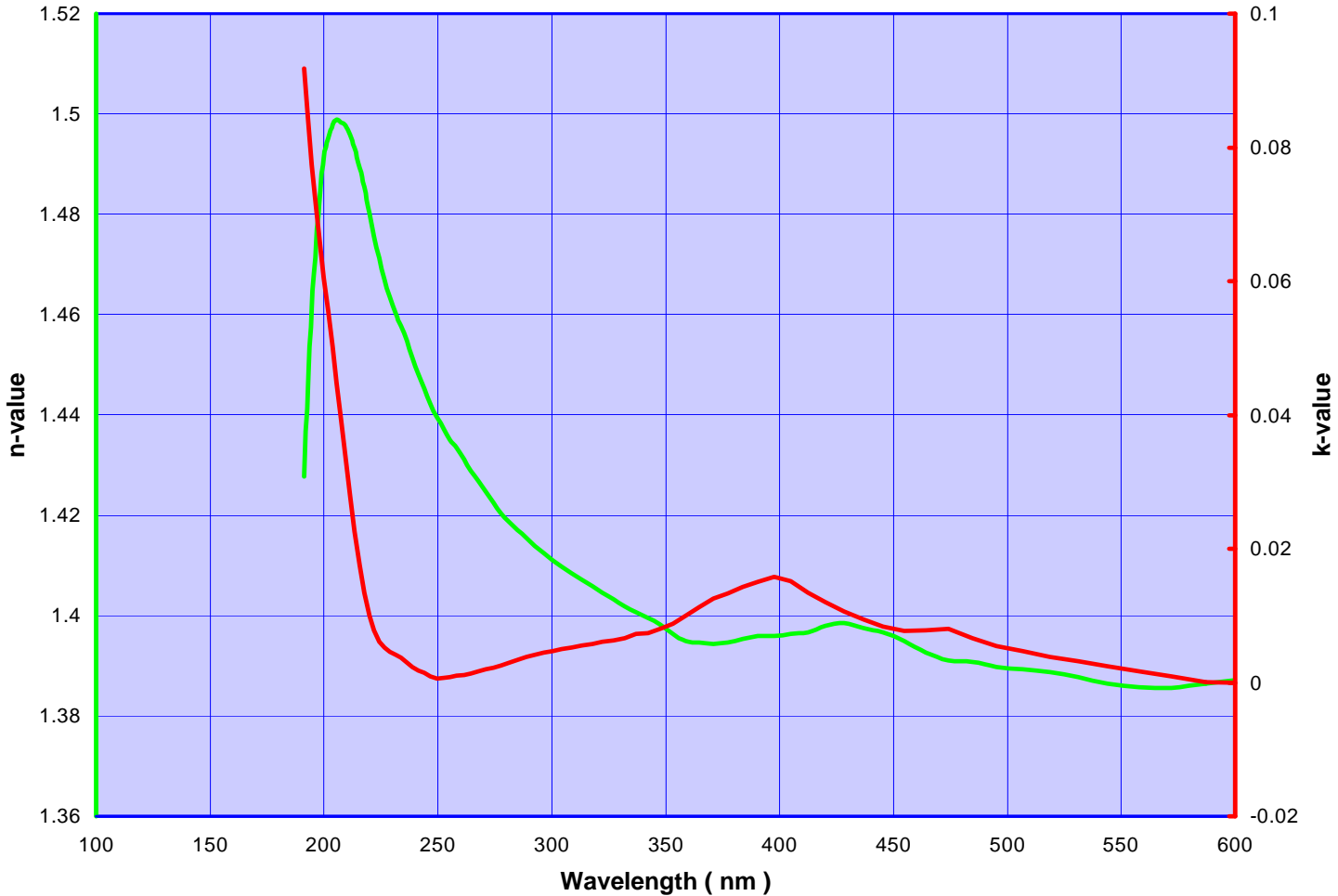
**70% Improvement in Cpk**

# AZ AQUATAR-VI-A Series Spin Curve



# Optical Parameters, n/k value

## AZ AQUATAR-VI-A



# Swing Suppression Effect

## AZ AX1050P with and without AZ AQUATAR-VI-A

